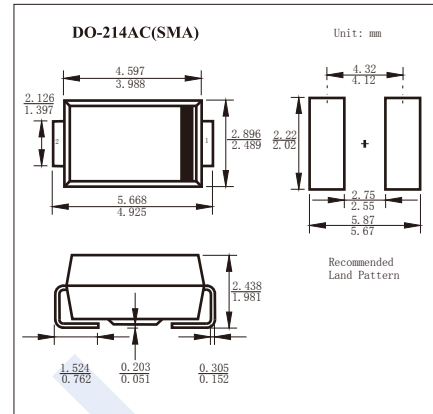


Schottky Diodes

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■ Features

- For surface mounted applications.
- Low profile package.
- Built-in strain relief.
- Metal silicon junction, majority carrier conduction.
- Low power loss, high efficiency.
- High current capability, low forward voltage drop.
- High surge capability.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Ratings	Unit
Maximum repetitive peak reverse voltage	V_{RRM}	80	V
Maximum RMS voltage	V_{RMS}	57	V
Maximum DC blocking voltage	V_{DC}	80	V
Maximum average forward rectified current at TL	$I_{(AV)}$	2.0	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	50.0	A
Maximum instantaneous forward voltage at 2.0A * 1	V_F	0.85	V
Maximum DC reverse current * 1 $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=100^\circ\text{C}$	I_R	0.2 10.0	mA
Typical thermal resistance	$R_{\theta JA}$ $R_{\theta JL}$	88.0 28.0	$^\circ\text{C}/\text{W}$
Operating junction temperature range	T_J	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-65 to +150	$^\circ\text{C}$

* 1. Pulse test: 300 μs pulse width, 1% duty cycle.

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■ Typical Characteristics

FIG.1-FORWARD CURRENT DERATING CURVE

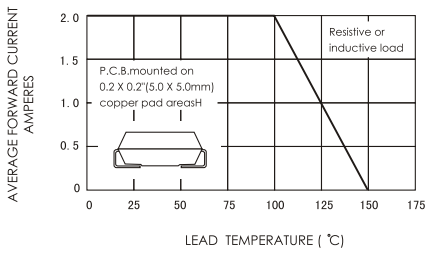


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

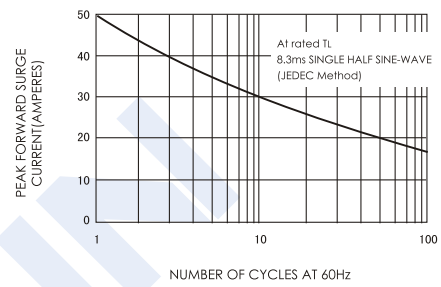


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

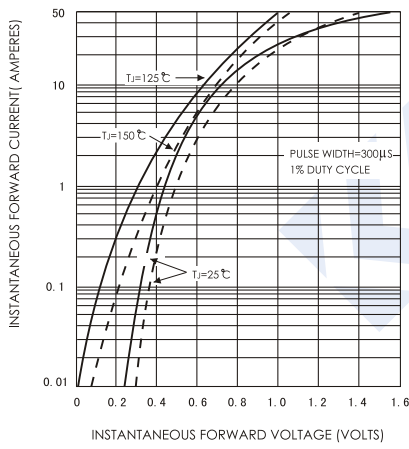


FIG.4-TYPICAL REVERSE CHARACTERISTICS

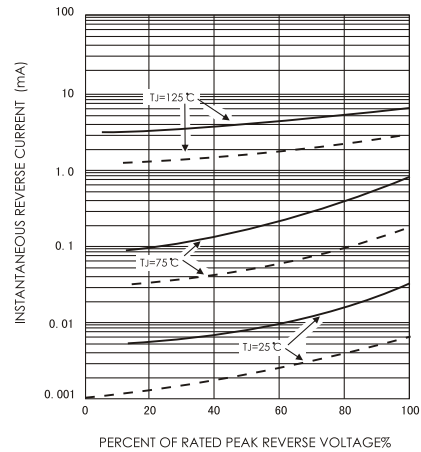


FIG.5-TYPICAL JUNCTION CAPACITANCE

